UNCLAMPED COLLECTOR–TO–EMITTER AVALANCHE CHARACTERISTICS ($-55° \le T_J \le 175°C$)

Characteristic	Symbol	Value	Unit
Single Pulse Collector–to–Emitter Avalanche Energy V_{CC} = 50 V, V_{GE} = 5.0 V, Pk I_L = 22 A, R_G = 1000 Ω, L = 1.8 mH, Starting T_J = 25°C V_{CC} = 50 V, V_{GE} = 5.0 V, Pk I_L = 17 A, R_G = 1000 Ω, L = 3.0 mH, Starting T_J = 25°C V_{CC} = 50 V, V_{GE} = 5.0 V, Pk I_L = 19 A, R_G = 1000 Ω, L = 1.8 mH, Starting T_J = 125°C	E_{AS}	 435 433 325	mJ
Reverse Avalanche Energy V_{CC} = 100 V, V_{GE} = 20 V, Pk I_L = 25.8 A, L = 6.0 mH, Starting T_J = 25°C	$E_{AS(R)}$	2000	mJ

THERMAL CHARACTERISTICS

Thermal Resistance, Junction to Case		$R_{\theta JC}$	1.3	°C/W
Thermal Resistance, Junction to Ambient	DPAK (Note 1)	$R_{\theta JA}$	95	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8″ from case for 5 seconds		T_L	275	°C

1. When surface mounted to an FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Collector–Emitter Clamp Voltage	BV_{CES}	I_C = 2.0 mA	T_J = –40°C to 150°C	380	395	420	V_{DC}
		I_C = 10 mA	T_J = –40°C to 150°C	390	405	430	
Zero Gate Voltage Collector Current	I_{CES}	V_{CE} = 350 V, V_{GE} = 0 V	T_J = 25°C	–	1.5	5	μA_{DC}
			T_J = 150°C	–	10	30*	
			T_J = –40°C	–	0.5	2.5	
		V_{CE} = 15 V, V_{GE} = 0 V	T_J = 25°C	–	–	2.0	
Reverse Collector–Emitter Leakage Current	I_{ECS}	V_{CE} = –24 V	T_J = 25°C	–	0.7	1.0	mA
			T_J = 150°C	–	12	25*	
			T_J = –40°C	–	0.1	1.0	
Reverse Collector–Emitter Clamp Voltage	$B_{VCES(R)}$	I_C = –75 mA	T_J = 25°C	27	33	37	V_{DC}
			T_J = 150°C	30	36	40	
			T_J = –40°C	25	32	35	
Gate–Emitter Clamp Voltage	BV_{GES}	I_G = 5.0 mA	T_J = –40°C to 150°C	11	13	15	V_{DC}
Gate–Emitter Leakage Current	I_{GES}	V_{GE} = 10 V	T_J = –40°C to 150°C	384	640	700	μA_{DC}
Gate Emitter Resistor (Note 3)	R_{GE}	–	T_J = –40°C to 150°C	10	16	26	kΩ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
*Maximum Value of Characteristic across Temperature Range.

ELECTRICAL CHARACTERISTICS (continued)

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	$V_{GE(th)}$	I_C = 1.0 mA, V_{GE} = V_{CE}	T_J = 25°C	1.2	1.5	1.8	V_{DC}
			T_J = 150°C	0.8	1.0	1.3	
			T_J = –40°C	1.4	1.7	2.0*	
Threshold Temperature Coefficient (Negative)	–	–	–	–	3.4	–	mV/°C
Collector–to–Emitter On–Voltage	$V_{CE(on)}$	I_C = 6.0 A, V_{GE} = 4.0 V	T_J = 25°C	1.0	1.2	1.5	V_{DC}
			T_J = 150°C	1.0	1.2	1.5	
			T_J = –40°C	1.0	1.2	1.5*	
		I_C = 8.0 A, V_{GE} = 4.0 V	T_J = 25°C	1.2	1.4	1.6*	
			T_J = 150°C	1.2	1.4	1.6	
			T_J = –40°C	1.2	1.4	1.6*	
		I_C = 10 A, V_{GE} = 4.0 V	T_J = 25°C	1.3	1.5	1.8	
			T_J = 150°C	1.3	1.5	1.9	
			T_J = –40°C	1.3	1.6	1.8*	
		I_C = 15 A, V_{GE} = 4.0 V	T_J = 25°C	1.7	1.9	2.3	
			T_J = 150°C	1.9	2.2	2.5*	
			T_J = –40°C	1.5	1.9	2.3	
		I_C = 10 A, V_{GE} = 4.5 V	T_J = 25°C	1.3	1.5	1.8*	
			T_J = 150°C	1.3	1.5	1.8*	
			T_J = –40°C	1.3	1.5	1.8*	
		I_C = 6.5 A, V_{GE} = 3.7 V	T_J = 25°C	–	–	1.65	
Forward Transconductance	gfs	V_{CE} = 5.0 V, I_C = 6.0 A	T_J = –40°C to 150°C	8.0	14	25	Mhos
DYNAMIC CHARACTERISTICS (Note 3)							
Input Capacitance	C_{ISS}	V_{CC} = 25 V, V_{GE} = 0 V f = 1.0 MHz	T_J = –40°C to 150°C	400	800	1000	pF
Output Capacitance	C_{OSS}			50	75	100	
Transfer Capacitance	C_{RSS}			4.0	7.0	10	
SWITCHING CHARACTERISTICS (Note 3)							
Turn–Off Delay Time (Resistive)	$t_{d(off)}$	V_{CC} = 300 V, I_C = 6.5 A R_G = 1.0 kΩ, R_L = 46 Ω,	T_J = 25°C	–	4.0	10	μSec
Fall Time (Resistive)	t_f	V_{CC} = 300 V, I_C = 6.5 A R_G = 1.0 kΩ, R_L = 46 Ω,	T_J = 25°C	–	9.0	15	
Turn–On Delay Time	$t_{d(on)}$	V_{CC} = 10 V, I_C = 6.5 A R_G = 1.0 kΩ, R_L = 1.5 Ω	T_J = 25°C	–	0.7	4.0	μSec
Rise Time	t_r	V_{CC} = 10 V, I_C = 6.5 A R_G = 1.0 kΩ, R_L = 1.5 Ω	T_J = 25°C	–	4.5	7.0	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

*Maximum Value of Characteristic across Temperature Range.

2. Pulse Test: Pulse Width ≤ 300 μS, Duty Cycle ≤ 2%.
3. Not production tested.

TYPICAL ELECTRICAL CHARACTERISTICS

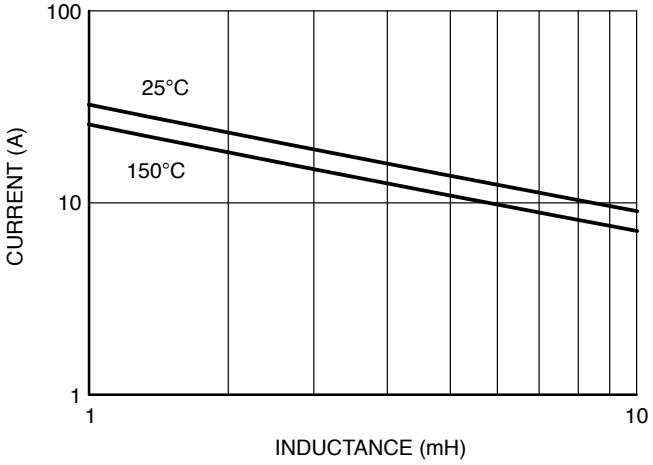


Figure 1. Maximum Single Pulse Switch Off Current vs. Inductance

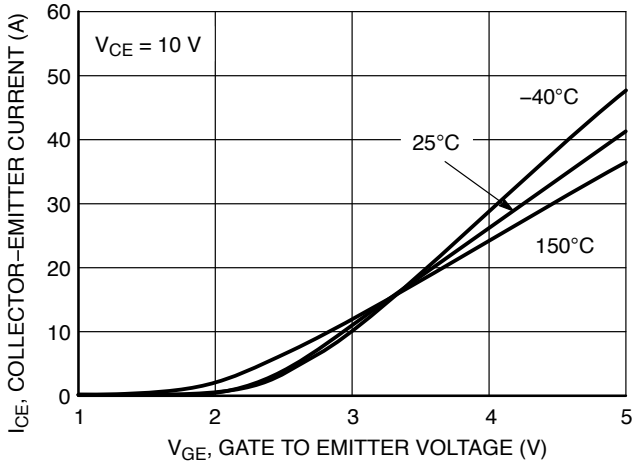


Figure 2. Transfer Characteristics

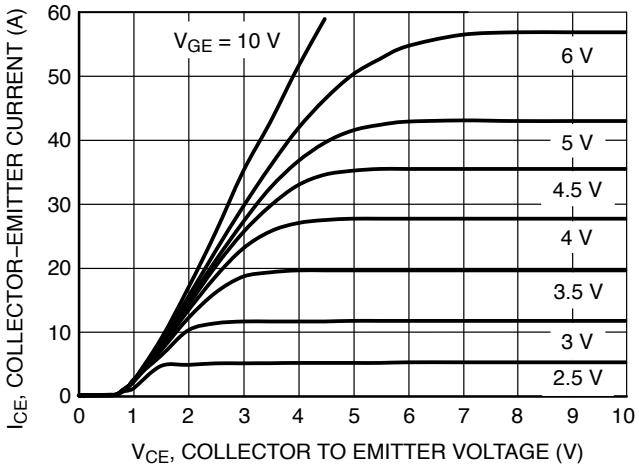


Figure 3. Output Characteristics, T_J = 25°C

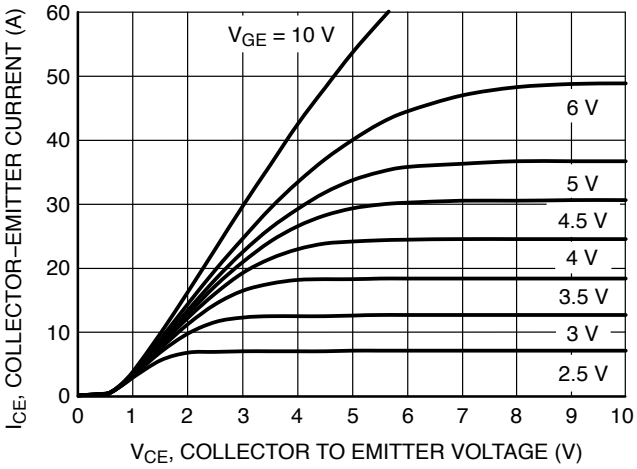


Figure 4. On−Region Characteristics, T_J = 150°C

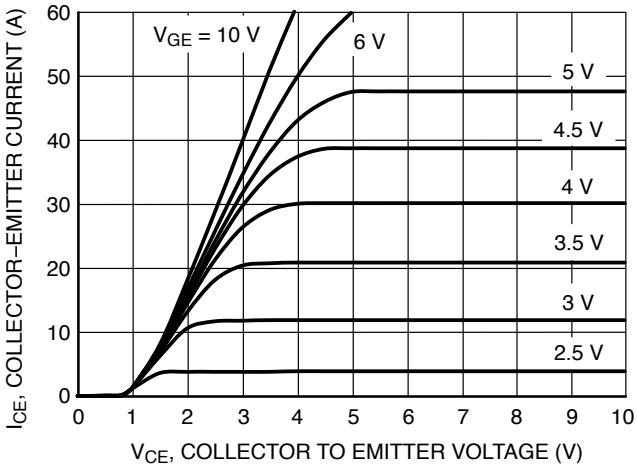


Figure 5. On−Region Characteristics, T_J = −40°C

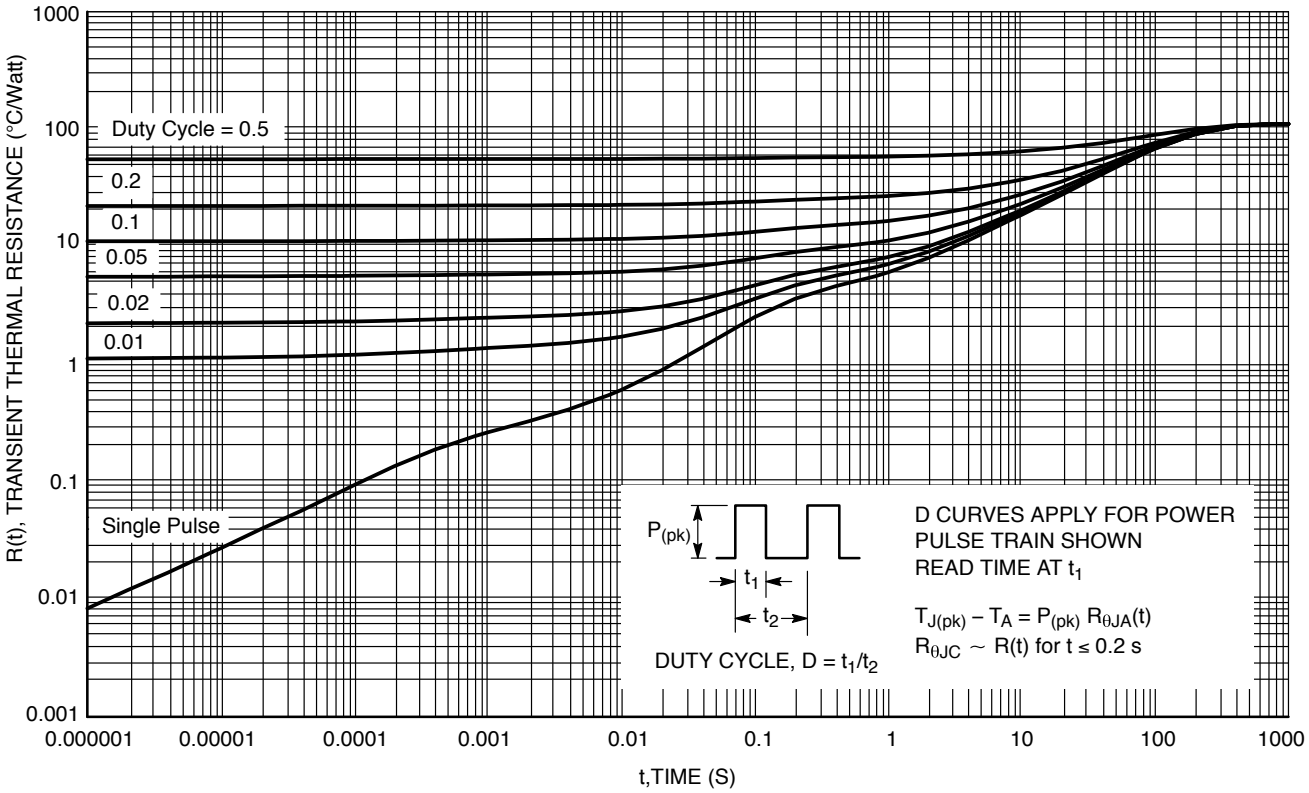
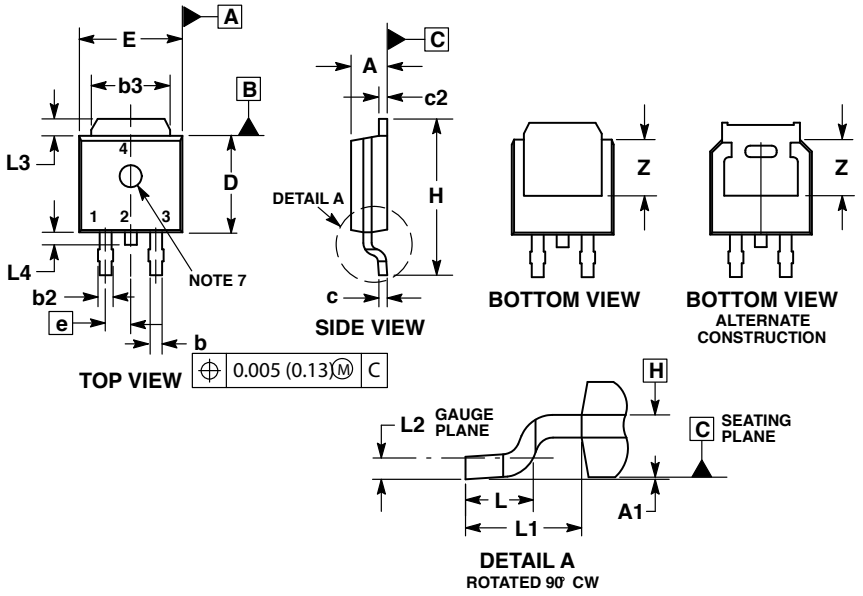


Figure 6. Transient Thermal Resistance (Non−normalized Junction−to−Ambient mounted on minimum pad area)

PACKAGE DIMENSIONS

DPAK
CASE 369C
ISSUE E

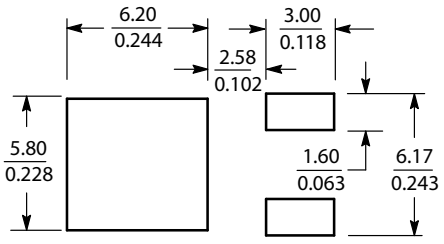


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

SOLDERING FOOTPRINT



SCALE 3:1 (mm / inches)

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